

## Features

- ESD Protected Up To 2KV (HBM)
- Trench LV MOSFET Technology
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device <sup>(Note 1)</sup>
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## Maximum Ratings

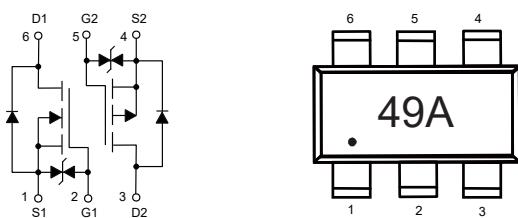
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 400°C/W Junction to Ambient <sup>(Note 2)</sup>

Parameter	Symbol	Rating	Unit
Total Power Dissipation <sup>(Note 4)</sup>	P <sub>D</sub>	312	mW
<b>N-Channel MOSFET</b>			
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current T <sub>A</sub> =25°C	I <sub>D</sub>	0.75	A
T <sub>A</sub> =100°C		0.47	
Pulsed Drain Current <sup>(Note 3)</sup>	I <sub>DM</sub>	3	A
<b>P-Channel MOSFET</b>			
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current T <sub>A</sub> =25°C	I <sub>D</sub>	-0.6	A
T <sub>A</sub> =100°C		-0.38	
Pulsed Drain Current <sup>(Note 3)</sup>	I <sub>DM</sub>	-2.4	A

Note:

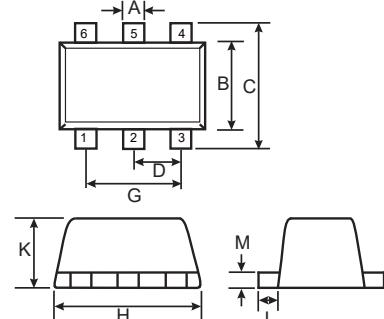
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P<sub>D</sub> is based on max. junction temperature, using junction-ambient thermal resistance.

## Internal Structure and Marking Code



## Dual N&P-Channel MOSFET

SOT-563



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.006	0.011	0.15	0.30	
B	0.043	0.051	1.10	1.30	
C	0.059	0.067	1.50	1.70	
D	0.020		0.50		TYP.
G	0.035	0.043	0.90	1.10	
H	0.059	0.067	1.50	1.70	
K	0.022	0.026	0.55	0.65	
L	0.004	0.011	0.10	0.30	
M	0.004	0.007	0.10	0.18	

**N-Channel ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	0.74	1.1	V
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V			±10	μA
Zero Gate Voltage Drain Current	I <sub>DS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =500mA		200	300	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =400mA		280	400	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =200mA		520	700	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =500mA		1.6		S
Gate Resistance	R <sub>g</sub>	f=1 MHz, Open drain		18		Ω
<b>Diode Characteristics</b>						
Continuous Body Diode Current	I <sub>S</sub>				750	mA
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =500mA			1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =380mA, dI <sub>F</sub> /dt=100A/μs		7		ns
Reverse Recovery Charge	Q <sub>rr</sub>			1		nC
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V, f=1MHz		27		pF
Output Capacitance	C <sub>oss</sub>			10		
Reverse Transfer Capacitance	C <sub>rss</sub>			4.8		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =1A		0.6		nC
Gate-Source Charge	Q <sub>gs</sub>			0.13		
Gate-Drain Charge	Q <sub>gd</sub>			0.15		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V, R <sub>G</sub> =10Ω, I <sub>D</sub> =500mA		3		ns
Turn-On Rise Time	t <sub>r</sub>			4		
Turn-Off Delay Time	t <sub>d(off)</sub>			7		
Turn-Off Fall Time	t <sub>f</sub>			4		

**P-Channel ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250µA	-20			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250µA	-0.5	-0.65	-1.1	V
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V			±10	µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	µA
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-500mA		0.66	0.85	Ω
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-300mA		0.95	1.2	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-200mA		1.4	2	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-500mA		1		S
Gate Resistance	R <sub>g</sub>	f=1 MHz, Open drain		30		Ω
<b>Diode Characteristics</b>						
Continuous Body Diode Current	I <sub>S</sub>				-0.6	A
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-500mA			-1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =-380mA, dI <sub>F</sub> /dt=100A/µs		9		ns
Reverse Recovery Charge	Q <sub>rr</sub>			2.3		nC
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V, f=1MHz		36		pF
Output Capacitance	C <sub>oss</sub>			11		
Reverse Transfer Capacitance	C <sub>rss</sub>			5.8		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1A		1.3		nC
Gate-Source Charge	Q <sub>gs</sub>			0.4		
Gate-Drain Charge	Q <sub>gd</sub>			0.2		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-10V, V <sub>GS</sub> =-4.5V, R <sub>G</sub> =10Ω, I <sub>D</sub> =-0.5A		6		ns
Turn-On Rise Time	t <sub>r</sub>			6		
Turn-Off Delay Time	t <sub>d(off)</sub>			11		
Turn-Off Fall Time	t <sub>f</sub>			6		

## Curve Characteristics (N-Channel)

Fig.1 - Typical Output Characteristics

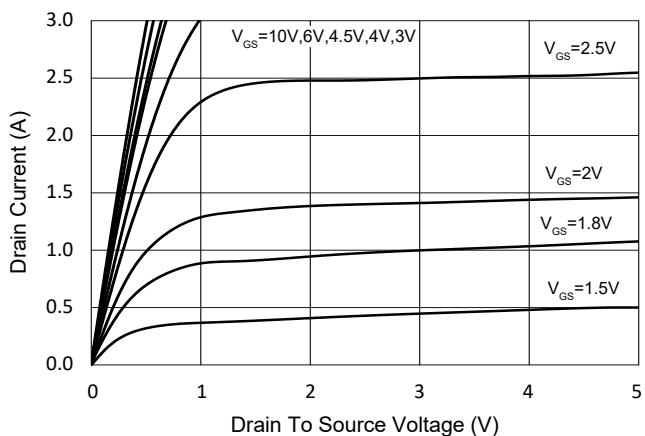


Fig.2 - Transfer Characteristic

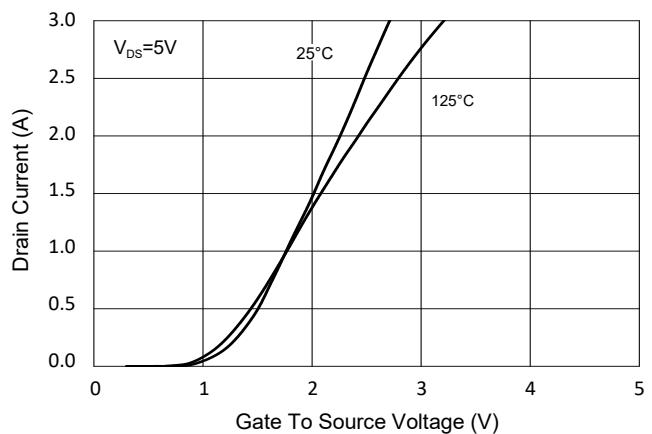


Fig.3 -  $R_{DS(ON)}$  -  $V_{GS}$

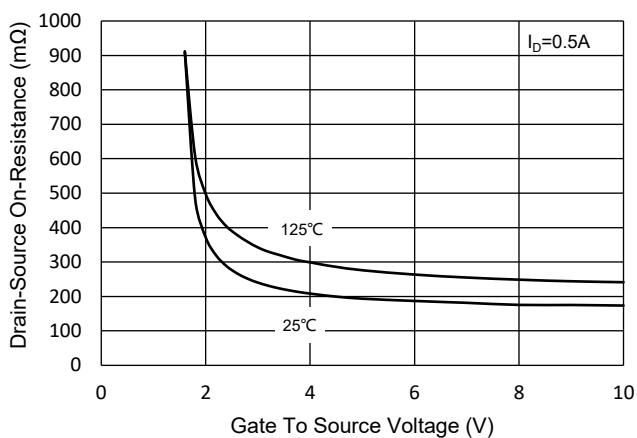


Fig.4 -  $R_{DS(ON)}$  -  $I_D$

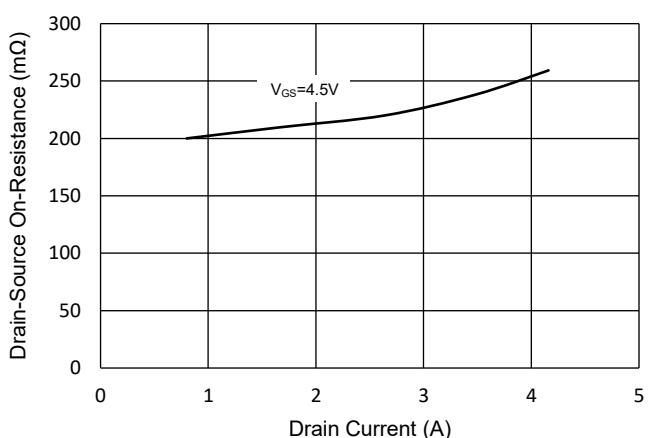


Fig.5 - Capacitance Characteristics

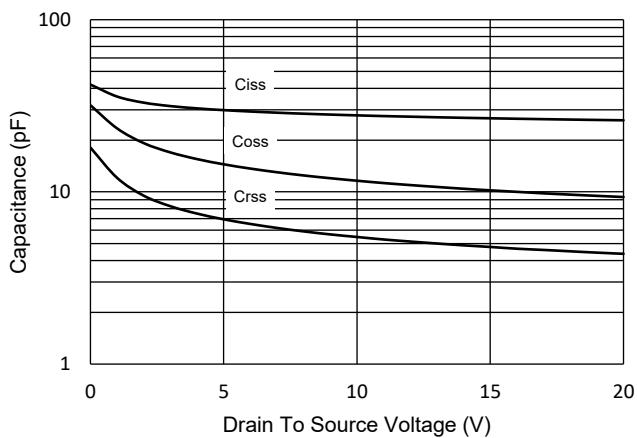
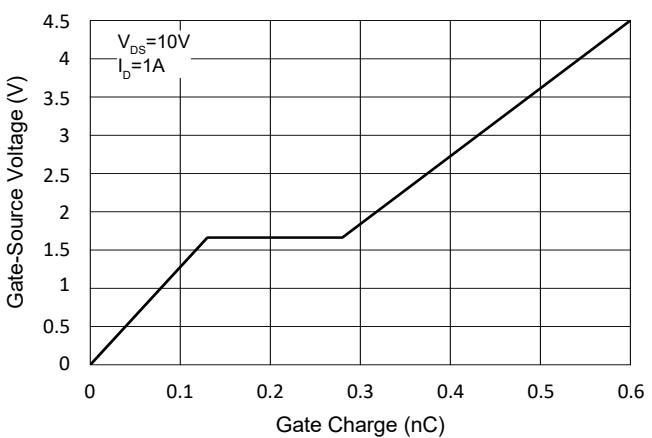


Fig.6 - Gate Charge



## Curve Characteristics (N-Channel)

Fig.7 - Normalized Threshold Voltage

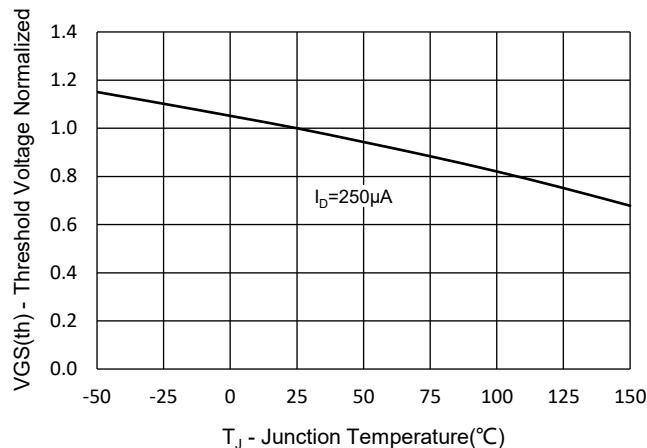


Fig.8 - Normalized On Resistance Characteristics

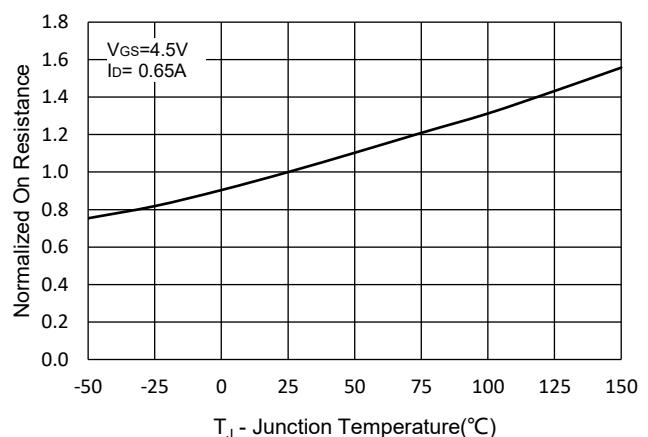


Fig.9 -  $I_S$  -  $V_{SD}$

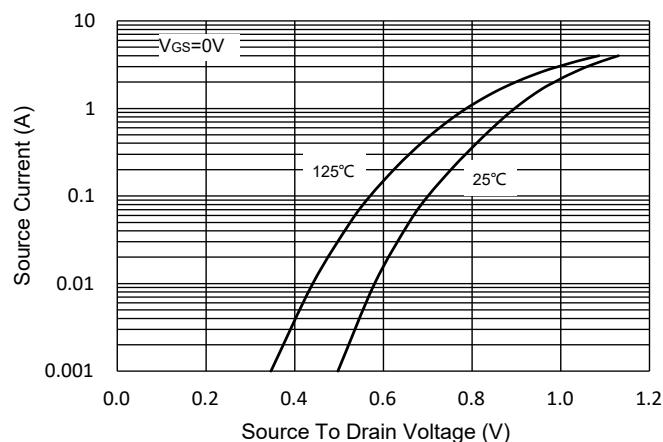


Fig.10 - Drain Current

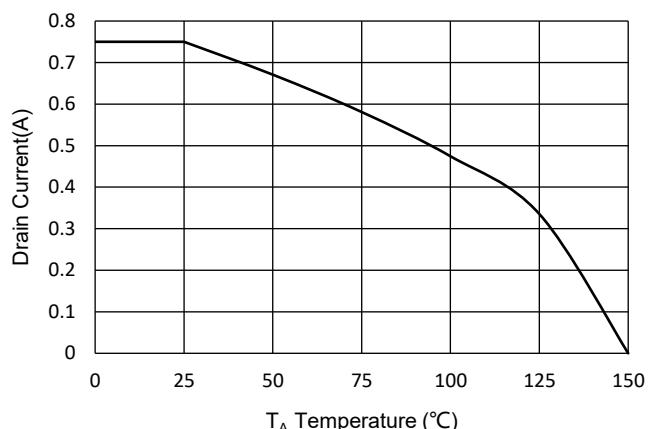
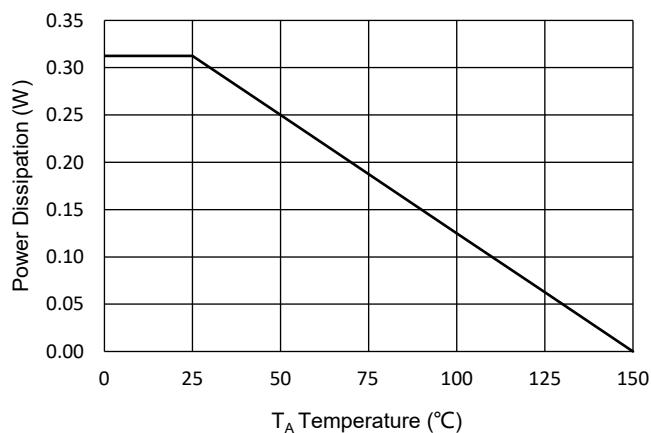


Fig.11 - PD Dissipation



## Curve Characteristics (N-Channel)

Fig.12 - Safe Operation Area

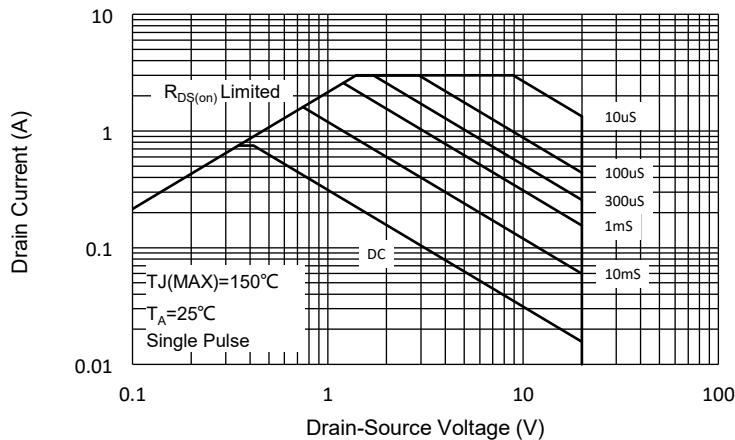
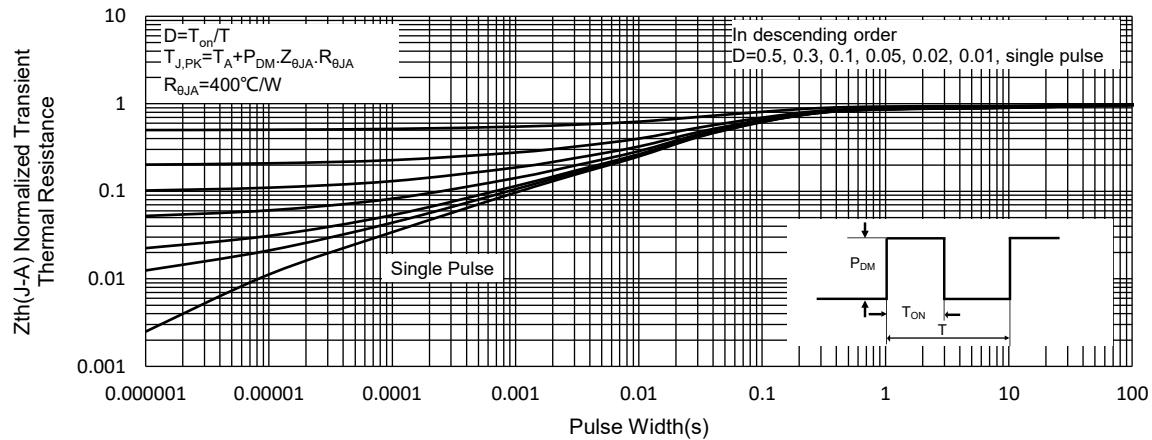
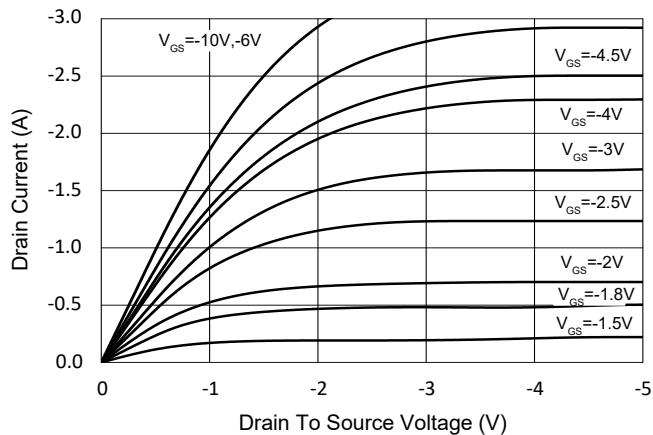


Fig.13 - Normalized Transient Thermal Impedance

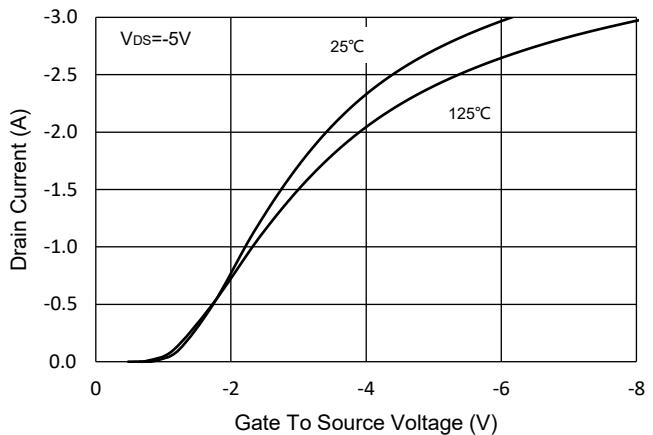


## Curve Characteristics (P-Channel)

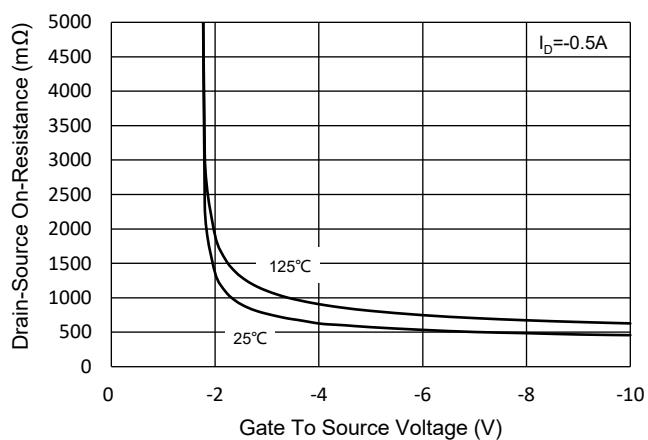
**Fig.1 - Typical Output Characteristics**



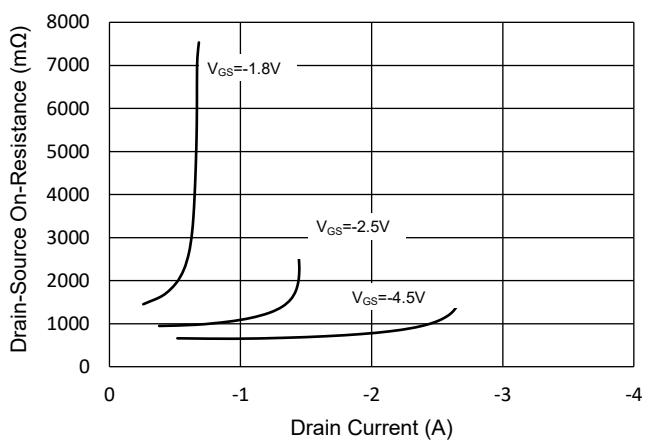
**Fig.2 - Transfer Characteristic**



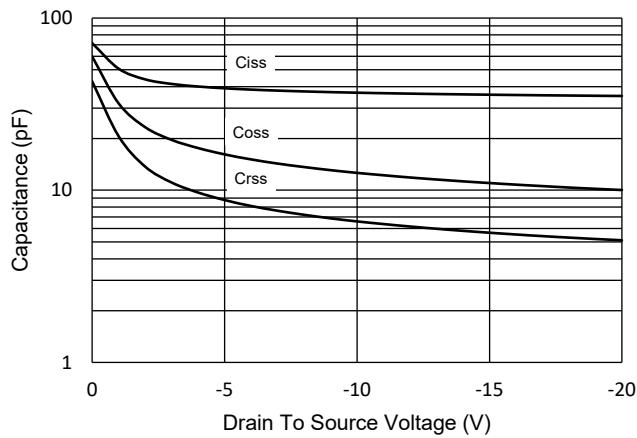
**Fig.3 -  $R_{DS(ON)}$  -  $V_{GS}$**



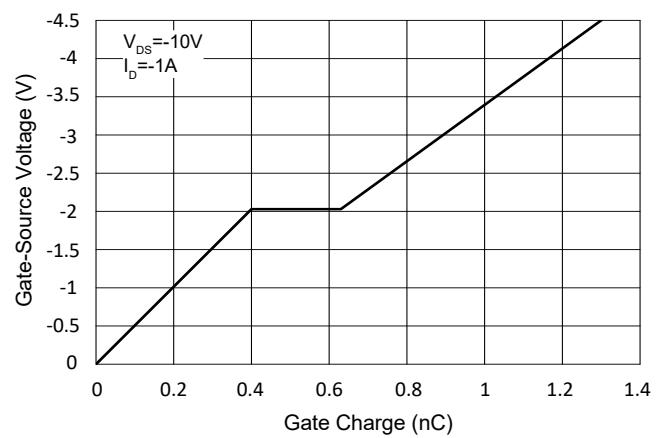
**Fig.4 -  $R_{DS(ON)}$  -  $I_D$**



**Fig.5 - Capacitance Characteristics**



**Fig.6 - Gate Charge**



## Curve Characteristics (P-Channel)

Fig.7 - Normalized Threshold Voltage

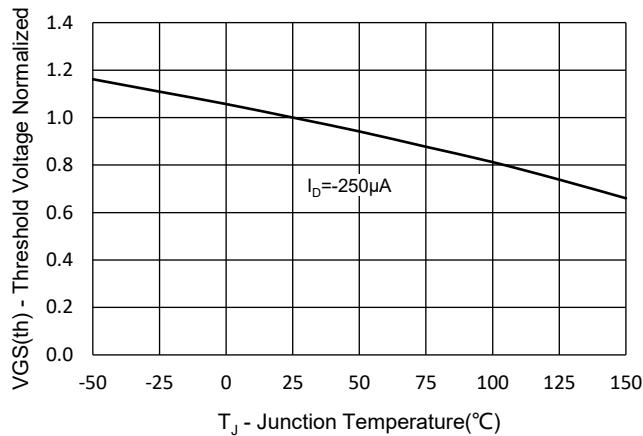


Fig.8 - Normalized On Resistance Characteristics

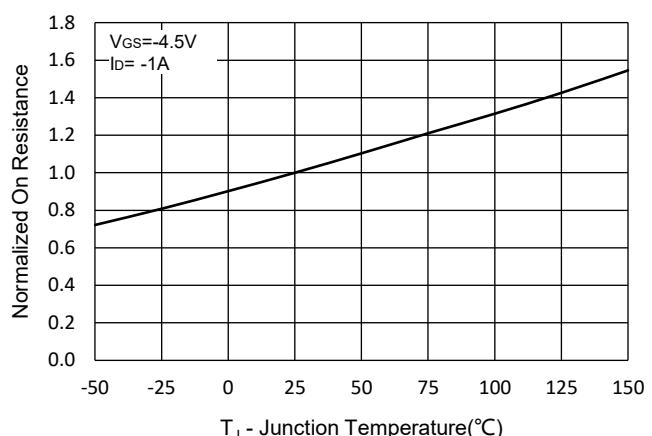


Fig.9 - I<sub>S</sub> - V<sub>SD</sub>

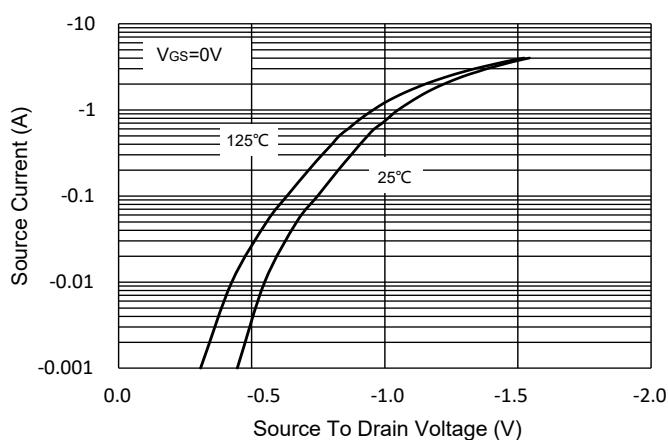


Fig.10 - Drain Current

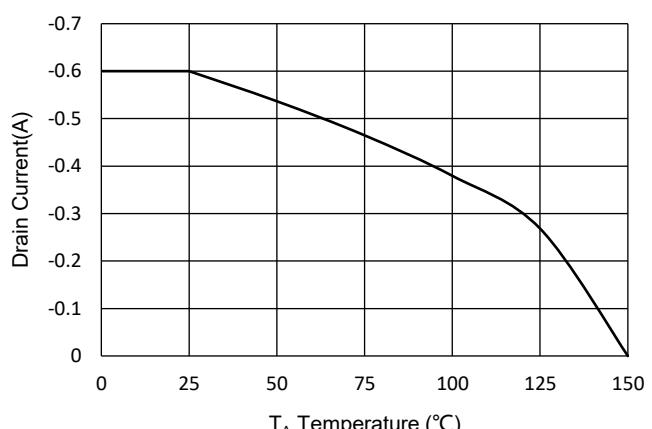
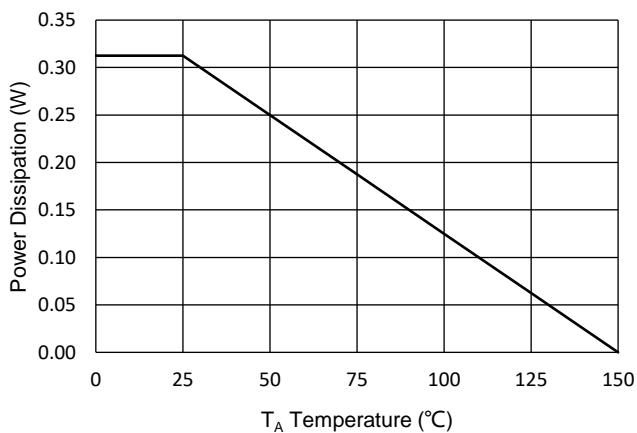


Fig.11 Power Dissipation



## Curve Characteristics (P-Channel)

Fig.12 - Safe Operation Area

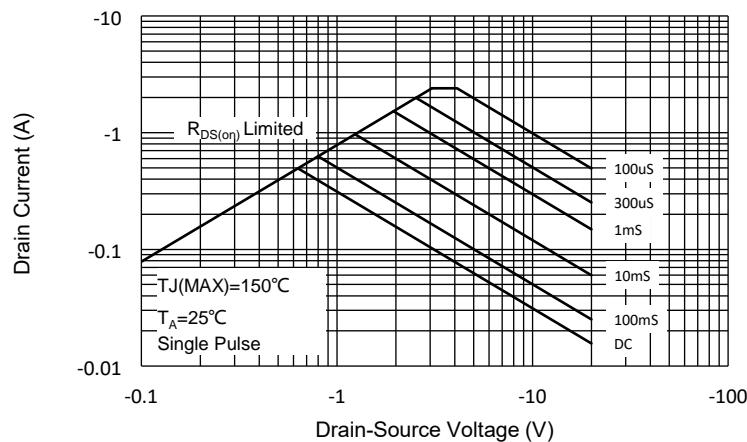
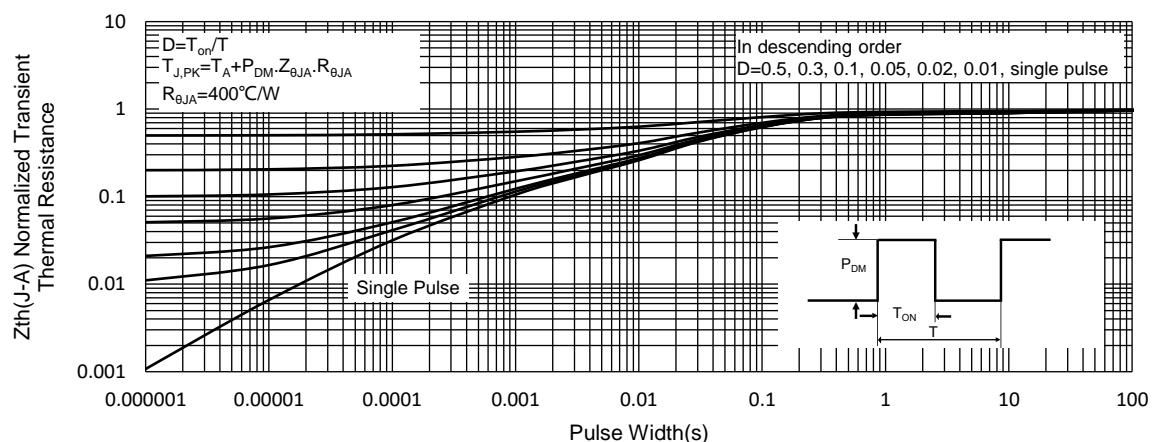


Fig.13 - Normalized Transient Thermal Impedance



## Ordering Information

Device	Packing
Part Number-TP	Tape&Reel:3Kpcs/Reel
Part Number-TPQ2	Tape&Reel:3Kpcs/Reel

For packaging details, go to our website at <https://www.mccsemi.com/pdf/ProductPackaging/SOT-563%20Package.pdf>

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